

# ABS Plastic-Encapsulate Bridge Rectifier

## Fast Recovery Bridge Rectifier

### Features

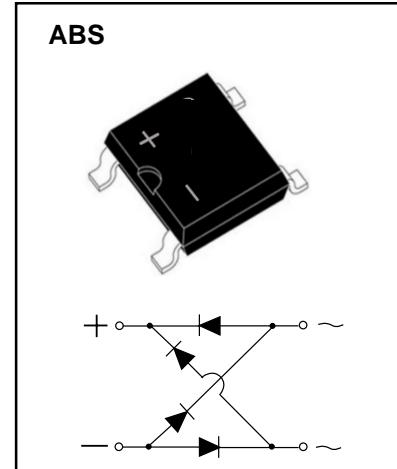
- $I_{F(AV)}$  2A
- $V_{RRM}$  1000V
- High surge current capability
- Glass passivated chip

### Applications

- General purpose 1 phase Bridge rectifier applications

### Marking

- RABS210



### Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions		RABS210
Repetitive Peak Reverse Voltage	$V_{RRM}$	V			1000
Maximum RMS Voltage	$V_{RMS}$	V			700
Maximum DC Blocking Voltage	$V_{DC}$	V			1000
Average Rectified Output Current	$I_O$	A	60Hz sine wave, R-load,Ta=60°C	On alumina substrate	2.0
Surge(Non-repetitive)Forward Current	$I_{FSM}$	A	8.3ms half sine wave, 1 cycle, $T_j=25^\circ C$		60
Current Squared Time	$I^2t$	$A^2S$	$t=8.3ms T_j=25^\circ C$ , Rating of per diode		14.94
Operation Junction and Storage Temperature Range	$T_J, T_{stg}$	°C			-55 ~+150

### Electrical Characteristics ( $T=25^\circ C$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	RABS210
Maximum Peak Forward Voltage	$V_{FM}$	V	$I_{FM}=2.0A$ , Pulse measurement, Rating of per diode	1.3
Maximum Peak Reverse Current	$I_{RRM}$	$\mu A$	$V_{RM}=V_{RRM}$ , Pulse measurement, Rating of per diode	5
MaximumPeak Reverse Current	trr	ns	$I_F=0.5A, I_R=1.0A, I_{rr}=0.25A$	500
Thermal Resistance	$R_{\theta J-A}$	°C/W	Between junction and ambient, On alumina substrate	75
	$R_{\theta J-L}$		Between junction and lead	25
	$R_{\theta J-C}$		Between junction and case	29
Junction Capacitance (Typical)	$C_J$	pF	Measured at 1MHZ and Applied Reverse Voltage of 4.0 V.D.C.	15

## Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

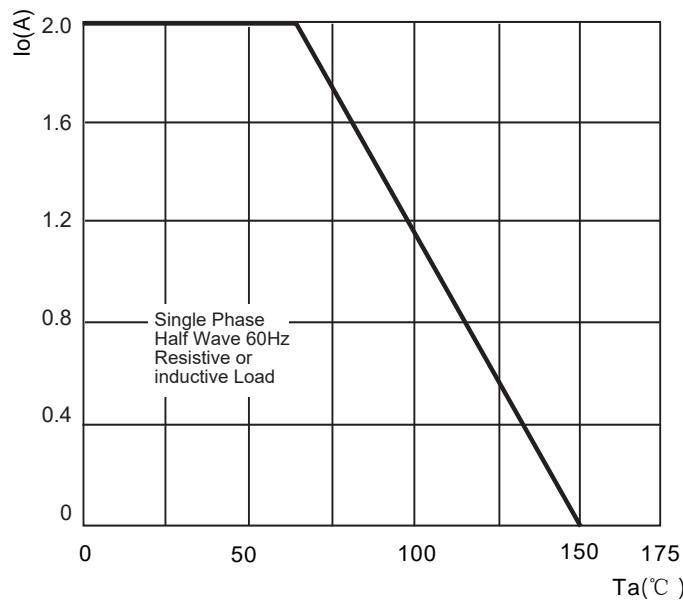


FIG.2: MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

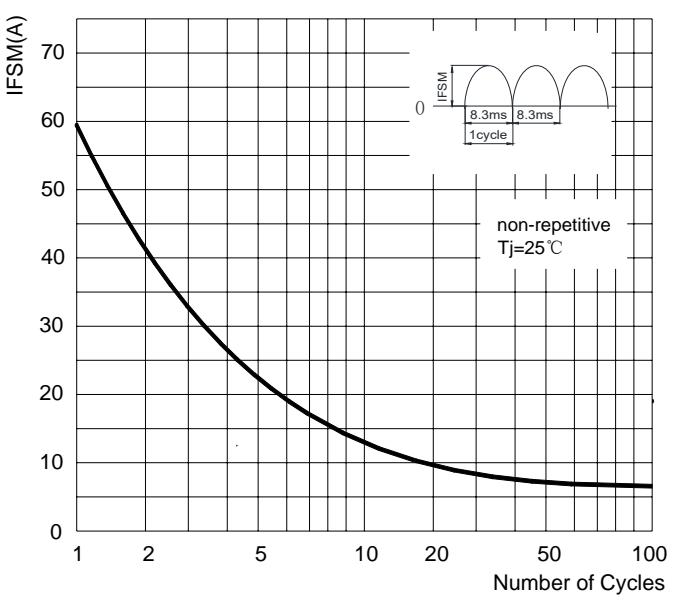


FIG.3: TYPICAL FORWARD CHARACTERISTICS

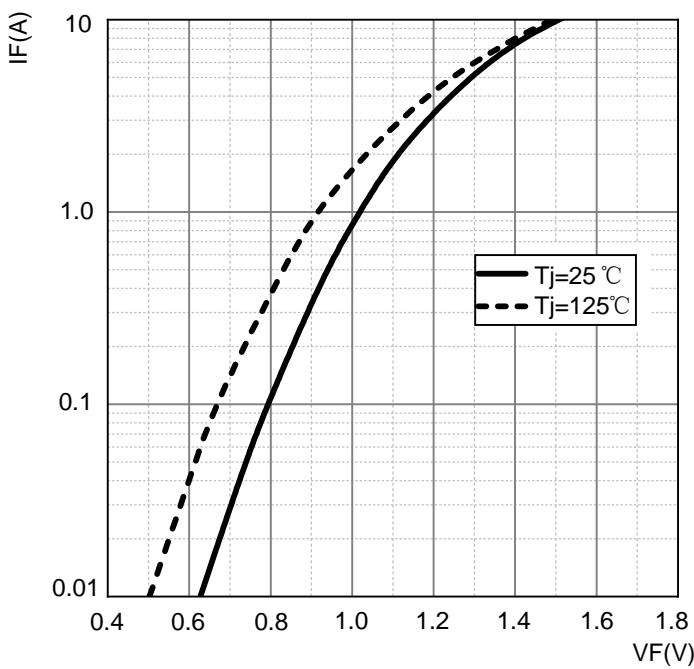
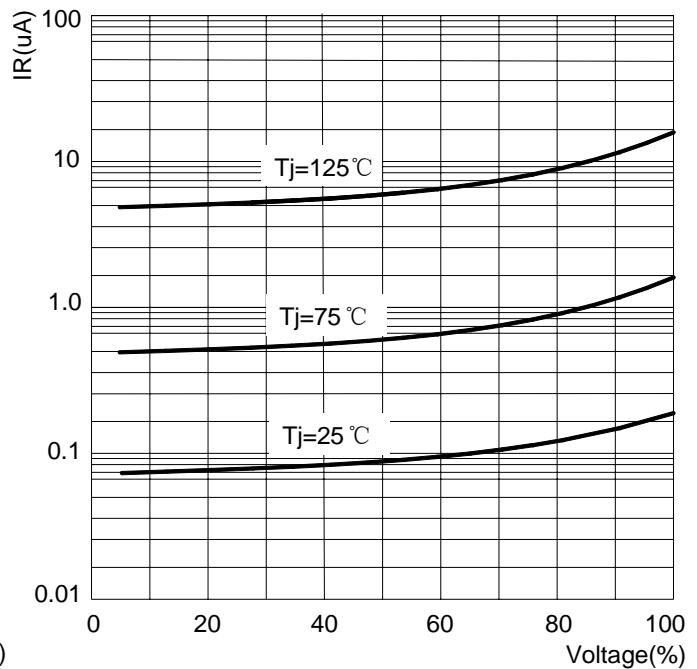
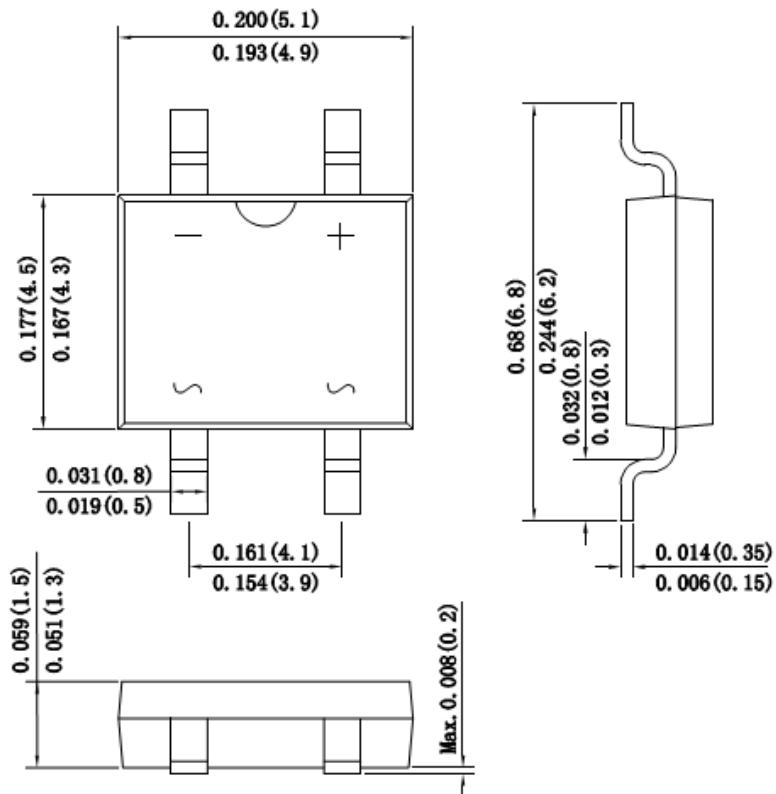


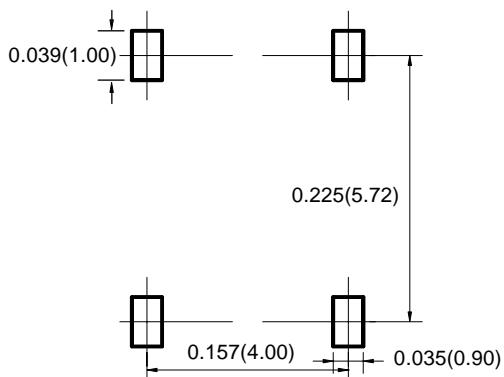
FIG.4: TYPICAL REVERSE CHARACTERISTICS



## ABS Package Outline Dimensions



## ABS Suggested Pad Layout



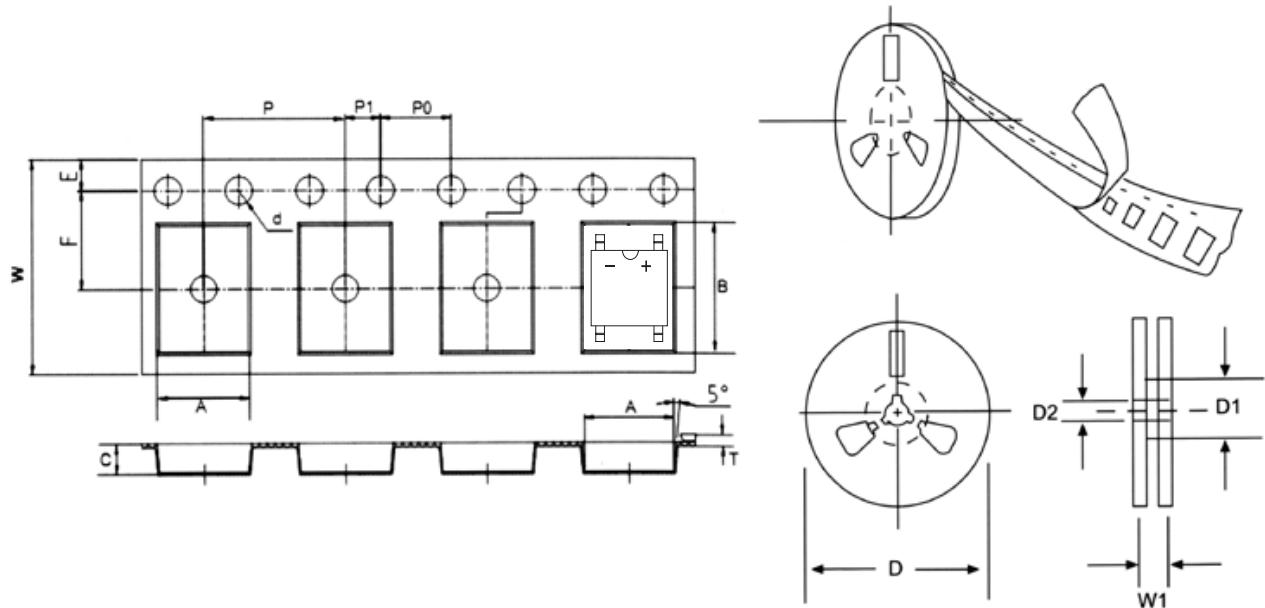
### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.

### NOTICE

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## Reel Taping Specifications For Surface Mount Devices-ABS



**FIG:CONFIGURATION OF SURFACE MOUNTED DEVICES TAPING**

ITEM	SYMBOL	ABS mm(inch)
Carrier width	A	5.40+0.1(0.213+0.004)
Carrier length	B	6.90+0.05(0.272+0.002)
Carrier depth	C	2.10+0.1(0.083+0.004)
Sprocket hole	d	1.55±0.05 (0.061±0.002)
Reel outside diameter	D	279±2.0 (11± 0.079)
Reel inner diameter	D1	75±1.0 ( 2.95 ±0.039)
Feed hole diameter	D2	13+0.5(0.512+0.020)
Strocket hole position	E	1.75+0.1(0.069+0.004)
Punch hole position	F	5.5+0.05(0.217+0.002)
Punch hole pitch	P	8.0+0.1(0.315+0.004)
Sprocket hole pitch	P0	4.0+0.1(0.157+0.004)
Embossment center	P1	2.0+0.1(0.079+0.004)
Total tape thickness	T	0.10-0.70(0.004-0.028)
Tape width	W	12.0+0.3/-0.1(0.472+0.004)
Reel width	W1	16.8+2.0(0.661+0.079)

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.